

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Application Serial No. 10/757,276
Filing Date January 14, 2004
Inventor Kevin L. Beaman et al.
Assignee Micron Technology, Inc.
Group Art Unit 2813
Examiner Stephen W. Smoot
Attorney's Docket No. MI22-2475
Customer No. 021567
Title: A Method of Forming a Structure Over a Semiconductor Substrate

EXAMINER INTERVIEW SUMMARY OF JUNE 28, 2007

To: Commissioner for Patents
P.O. Box 1450
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Applicant's representative held an interview with Examiner Smoot on June 28, 2007.

Applicant's representative would like to thank Examiner Smoot for his time and attention to this matter.

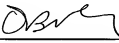
Agreement was reached to amend dependent claim 58 for consistency. Claim 58 will be amended in the following manner by Examiner's Amendment:

58. (by Examiner amendment) The method of claim 36 further comprising forming a silicide layer over at least one of the first and second layers comprising the conductively doped silicon.

Applicant's representative is greatly appreciative of the efforts and time put in to this matter by Examiner Smoot.

Respectfully submitted,

Dated: 6-28-07

By: 
D. Brent Kenady
Reg. No. 40,045